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Physics of Failure in Electronics

Volume 3

RELIABILITY SERIES

Edited by M. F. Goldberger

IIT Research Institute

and

Rome Air Development Center

Joseph Vaccaro

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Preface

This volume contains the proceedings of the 1964 Symposium on the Physics of Failure in Electronics held at the Illinois Institute of Technology in Chicago on 29 September-1 October 1964. This is the third of an annual series of symposia jointly sponsored by the Rome Air Development Center and IT Research Institute.

Introduction remarks were made at the opening session by V. H. Disney, on behalf of the IIT Research Institute, and an opening address was given by Brig. General A. T. Culbertson, Commander, Rome Air Development Center, USAF. A luncheon address was delivered by Col. A. C. Lowell (USMC, Ret.), President of General Microelectronics, Inc.

Session IV-Effects in Films

Session V-Bulk Effects

Session moderators were:

G. Henderson
Martin Company, Orlando, Florida

W. M. Redler
NASA Headquarters, Washington, D.C.

M. J. Ibers
Wright Air Development Center, USAF

Morton E. Goldberg
IIT Research Institute

David F. Barber
Rome Air Development Center, USAF

Session I-Test, Analysis, and Correlation

Session II-Surface Effects

Session III-Principles and Applications

Session IV-Effects in Films

Session V-Bulk Effects

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